# Octal D-Type Latch with 3-State Outputs

# With 5V–Tolerant Inputs

The MC74LVX373 is an advanced high speed CMOS octal latch with 3–state outputs. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

This 8-bit D-type latch is controlled by a latch enable input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

#### Features

- High Speed:  $t_{PD} = 5.8$  ns (Typ) at  $V_{CC} = 3.3$  V
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise:  $V_{OLP} = 0.8 V (Max)$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

• These Devices are Pb-Free and are RoHS Compliant



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DW SUFFIX CASE 751D DT SUFFIX CASE 948E

#### **PIN ASSIGNMENT**

	V <sub>CC</sub>	07	D7	D6	06	05	D5	D4	04	LE
_	20	19	18	17	16	15	14	13	12	11
	<b>)</b>									
	1	2	3	4	5	6	7	8	9	10
	ŌĒ	00	D0	D1	01	02	D2	D3	03	GND
				20-L	ead	(Тор	Viev	v)		
			MA	RKI	NG	DIAC	GRA	MS		
20	<u>A A F</u>	<u>1 A A</u>	<u>A A</u>	<u>A A</u>	£,	20	AB	AAF	188	AAA,
	A		X373 YWV					3	.VX 373 .YW∎	1



LVX373= Specific Device CodeA= Assembly LocationWL, L= Wafer LotY= YearWW, W= Work WeekG or •= Pb-Free Package

(Note: Microdot may be in either location)

#### **PIN NAMES**

Pins	Function
OE	Output Enable Input
LE	Latch Enable Input
D0-D7	Data Inputs
O0-O7	3–State Latch Outputs

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

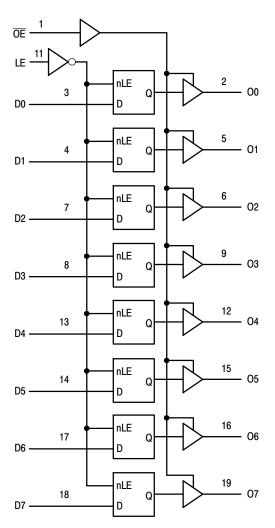


Figure 1. Logic Diagram

	INPUTS		OUTPUTS	
ŌĒ	LE	Dn	On	OPERATING MODE
L	ΗI	тч	Τ∟	Transparent (Latch Disabled); Read Latch
L	L	h I	H L	Latched (Latch Enabled) Read Latch
L	L	Х	NC	Hold; Read Latch
Н	L	Х	Z	Hold; Disabled Outputs
H H	H H	H L	Z Z	Transparent (Latch Disabled); Disabled Out- puts
H H	L	h I	Z Z	Latched (Latch Enabled); Disabled Outputs

H = High Voltage Level; h = High Voltage Level One Setup Time Prior to the Latch Enable High-to-Low Transition; L = Low Voltage Level; I = Low Voltage Level One Setup Time Prior to the Latch Enable High-to-Low Transition; NC = No Change, State Prior to the Latch Enable High-to-Low Transition; X = High or Low Voltage Level or Transitions are Acceptable; Z = High Impedance State; For I<sub>CC</sub> Reasons DO NOT FLOAT Inputs

#### MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V
Vin	DC Input Voltage	-0.5 to +7.0	V
Vout	DC Output Voltage	–0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Diode Current	-20	mA
I <sub>OK</sub>	Output Diode Current	±20	mA
l <sub>out</sub>	DC Output Current, per Pin	±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±75	mA
PD	Power Dissipation	180	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	3.6	V
V <sub>in</sub>	DC Input Voltage	0	5.5	V
Vout	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	-40	+85	°C
$\Delta t / \Delta V$	Input Rise and Fall Time	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

#### DC ELECTRICAL CHARACTERISTICS

			Vcc	Т	A = 25°	С	T <sub>A</sub> = -40	) to 85°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V <sub>IL</sub>	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V <sub>OH</sub>	High-Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	$\begin{split} I_{OH} &= -50 \; \mu A \\ I_{OH} &= -50 \; \mu A \\ I_{OH} &= -4 \; m A \end{split}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V <sub>OL</sub>	Low–Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	$I_{OL} = 50 \ \mu A$ $I_{OL} = 50 \ \mu A$ $I_{OL} = 4 \ m A$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
l <sub>in</sub>	Input Leakage Current	$V_{in} = 5.5 \text{ V or GND}$	3.6			±0.1		±1.0	μA
I <sub>OZ</sub>	Maximum 3-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	3.6			±0.2 5		±2.5	μΑ
I <sub>CC</sub>	Quiescent Supply Current	$V_{in} = V_{CC} \text{ or } GND$	3.6			4.0		40.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **AC ELECTRICAL CHARACTERISTICS** (Input $t_f = t_f = 3.0$ ns)

					A = 25°	c	$T_{A} = -40$	) to 85°C	
Symbol	Parameter	Test Con	ditions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay D to O	V <sub>CC</sub> = 2.7 V	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		7.5 10.0	14.5 18.0	1.0 1.0	17.5 21.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.8 8.3	9.3 12.8	1.0 1.0	11.0 14.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay LE to O	V <sub>CC</sub> = 2.7 V	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		7.7 10.2	15.0 18.5	1.0 1.0	18.5 22.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		6.0 8.5	9.7 13.2	1.0 1.0	11.5 15.0	
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time OE to O	$V_{CC} = 2.7 V$ $R_L = 1 k\Omega$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		7.7 10.2	15.0 18.5	1.0 1.0	18.5 22.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_{L} = 1 \text{ k}\Omega$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		6.0 8.5	9.7 13.2	1.0 1.0	11.5 15.0	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time OE to O	$V_{CC} = 2.7 V$ $R_L = 1 k\Omega$	C <sub>L</sub> = 50 pF		9.8	18.0	1.0	21.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_{L} = 1 \text{ k}\Omega$	C <sub>L</sub> = 50 pF		8.2	12.8	1.0	14.5	
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 1)	V <sub>CC</sub> = 2.7 V V <sub>CC</sub> = 3.3 ±0.3 V				1.5 1.5		1.5 1.5	ns

 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

#### **CAPACITIVE CHARACTERISTICS**

		T <sub>A</sub> = 25°C		T <sub>A</sub> = −40 to 85°C			
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
Cin	Input Capacitance		4	10		10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance		6				pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 2)		27				pF

2.  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/8$  (per latch).  $C_{PD}$  is used to determine the no-load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .

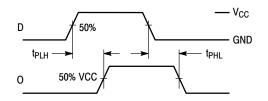
#### **NOISE CHARACTERISTICS** (Input $t_f = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 3.3$ V, Measured in SOIC Package)

			T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit	
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.5	0.8	V	
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.5	-0.8	V	
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V	
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V	

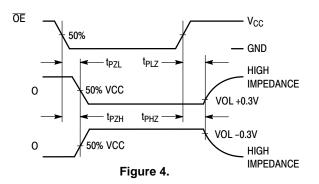
#### TIMING REQUIREMENTS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns)

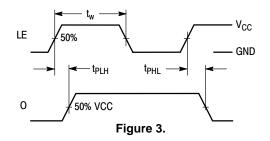
			T <sub>A</sub> =	25°C	$T_A = -40$ to $85^{\circ}C$	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Unit
t <sub>w(h)</sub>	Minimum Pulse Width, LE	$V_{CC} = 2.7 V$ $V_{CC} = 3.3 \pm 0.3 V$		6.5 5.0	7.5 5.0	ns
t <sub>su</sub>	Minimum Setup Time, D to LE	$V_{CC} = 2.7V$ $V_{CC} = 3.3 \pm 0.3 V$		6.0 4.0	6.0 4.0	ns
t <sub>h</sub>	Minimum Hold Time, D to LE	$V_{CC} = 2.7 V$ $V_{CC} = 3.3 \pm 0.3 V$		1.0 1.0	1.0 1.0	ns

### SWITCHING WAVEFORMS









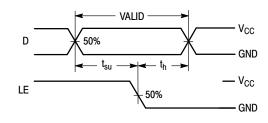
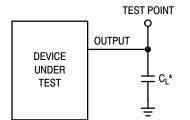


Figure 5.

## **TEST CIRCUITS**



\*Includes all probe and jig capacitance Figure 6. Propagation Delay Test Circuit

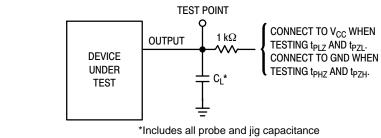
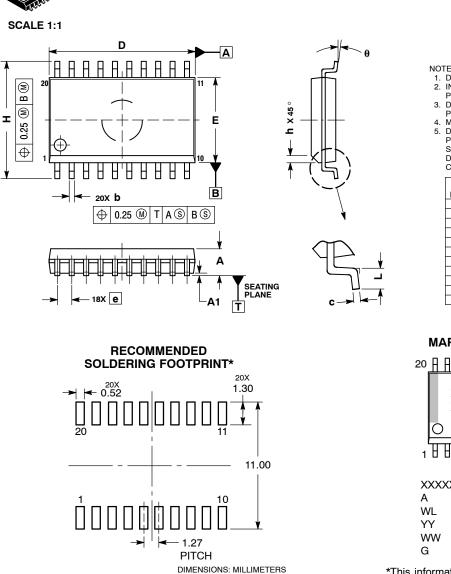


Figure 7. Three-State Test Circuit

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC74LVX373DWR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74LVX373DTR2G	TSSOP–20 (Pb–Free)	2500 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DUSEM

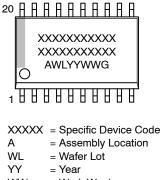
NOTES:

SOIC-20 WB CASE 751D-05 ISSUE H

- 1. DIMENSIONS ARE IN MILLIMETERS. 2. INTERPRET DIMENSIONS AND TOLERANCES
- PER ASME Y14.5M, 1994. 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
b	0.35	0.49			
C	0.23	0.32			
D	12.65	12.95			
Е	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0 °	7 °			

GENERIC **MARKING DIAGRAM\*** 



= Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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